

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	EV2SA1362-X-S1
▶ Overseas	Part Number	2SA1362-X
▶ Equivalent	Part Number	2SA1362-X

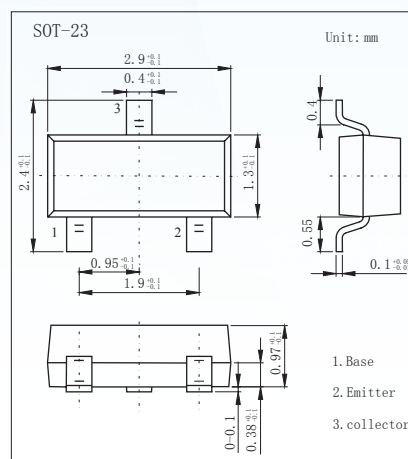
"S1" means SOT-23

EV is the abbreviation of name EVVO

PNP Transistors

■ Features

- Suitable for driver stage of small motor.
- Small package.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-15	V
Collector-emitter voltage	V_{CE0}	-15	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-800	mA
Base current	I_B	-160	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

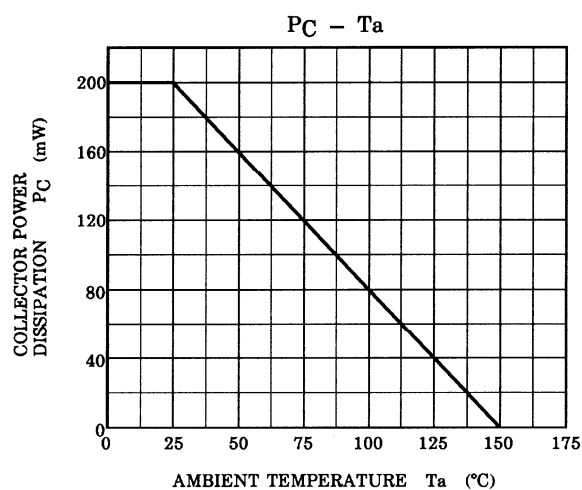
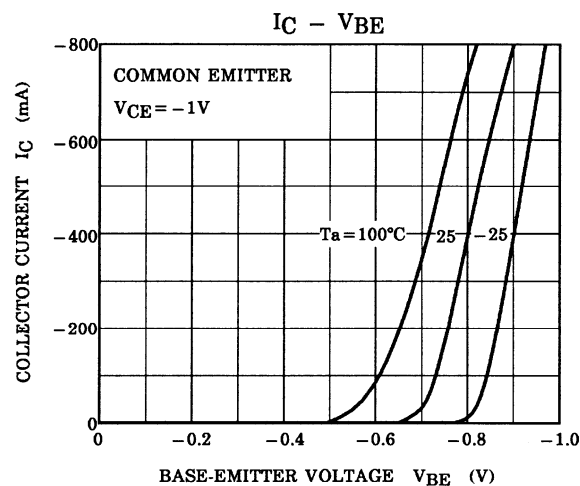
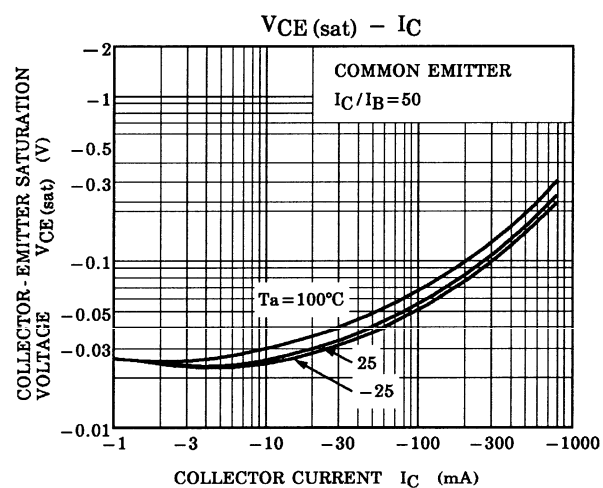
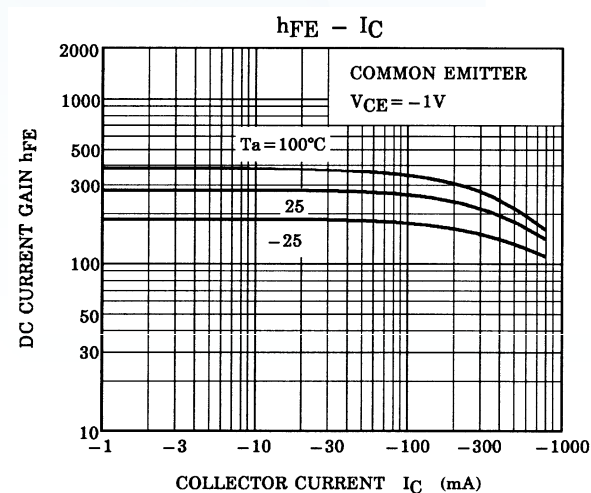
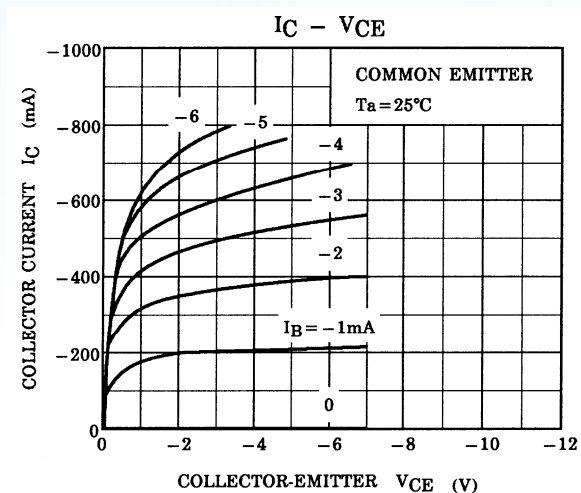
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}, I_E = 0$	-15			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -10 \text{ mA}, I_B = 0$	-15			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -15 \text{ V}, I_E = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -400 \text{ mA}, I_B = -8 \text{ mA}$			-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -400 \text{ mA}, I_B = -8 \text{ mA}$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -1 \text{ V}, I_C = -10 \text{ mA}$	-0.5		-0.8	
DC current gain	h_{FE}	$V_{CE} = -1 \text{ V}, I_C = -100 \text{ mA}$	120		400	
		$V_{CE} = -1 \text{ V}, I_C = -800 \text{ mA}$	40			
Common base output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		13		pF
Transition frequency	f_T	$V_{CB} = -5 \text{ V}, I_C = -10 \text{ mA}$		120		MHz

■ Classification of h_{FE}

Type	EV2SA1362-Y-S1	EV2SA1362-G-S1
Range	120-240	200-400
Marking	AEY	AEG

PNP Transistors

■ Typical Characteristics



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